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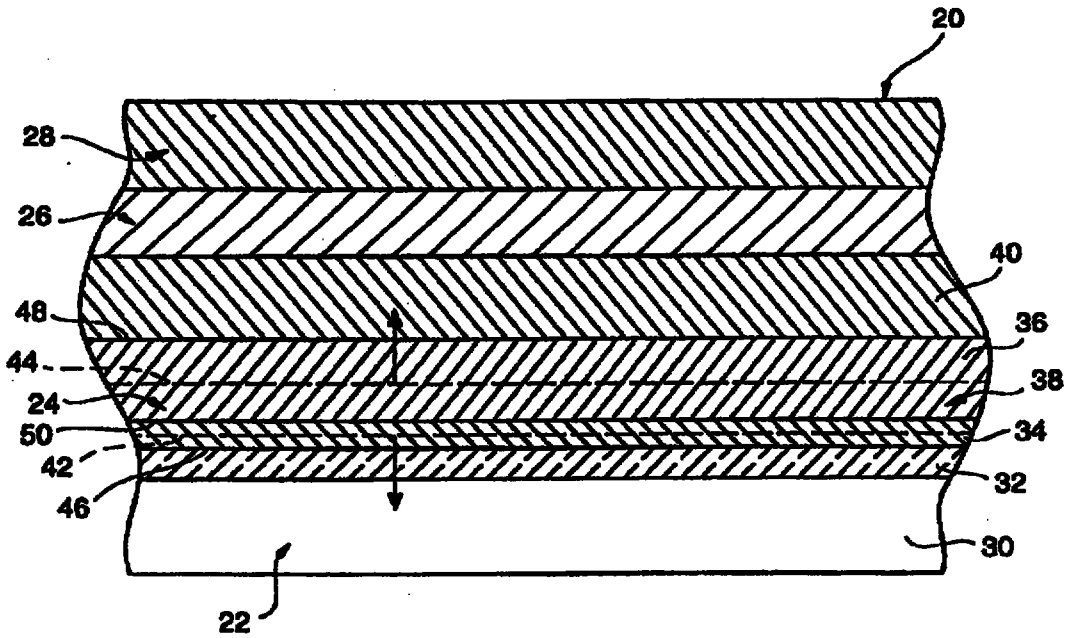
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(54) Title: BOTTOM ELECTRODE STRUCTURE FOR DIELECTRIC CAPACITORS AND METHOD OF MAKING THE SAME



(57) Abstract

An integrated circuit capacitor (20) includes a bottom electrode structure (24) having an adhesion metal portion (34), a noble metal portion (36), and a second noble metal layer (40). A process of manufacture includes annealing the adhesion metal portion (34) and the noble metal portion (36) prior to the deposition of second noble metal layer (40) for purposes of forming barrier region (38). The electrode (24) preferably contacts metal oxide layer (26), which is made of a perovskite or perovskite-like layered superlattice material. A temporary capping layer (59) is formed and removed in manufacture, which serves to increase polarization potential from the device by at least 40 %.